Low Voltage Single Supply Dual DPDT Analog Switch

The NLAS44599 is an advanced dual-independent CMOS double pole-double throw (DPDT) analog switch fabricated with silicon gate CMOS technology. It achieves high speed propagation delays and low ON resistances while maintaining CMOS low power dissipation. This DPDT controls analog and digital voltages that may vary across the full power–supply range (from $V_{\rm CC}$ to GND).

The device has been designed so the ON resistance (R_{ON}) is much lower and more linear over input voltage than R_{ON} of typical CMOS analog switches.

The channel select input is compatible with standard CMOS outputs. The channel select input structure provides protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. This input structure helps prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The NLAS44599 can also be used as a quad 2-to-1 multiplexerdemultiplexer analog switch with two Select pins that each controls two multiplexer-demultiplexers.

- Channel Select Input Over-Voltage Tolerant to 5.5 V
- Fast Switching and Propagation Speeds
- Break-Before-Make Circuitry
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- Diode Protection Provided on Channel Select Input
- Improved Linearity and Lower ON Resistance over Input Voltage
- Latch-up Performance Exceeds 300 mA
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Chip Complexity: 158 FETs
- Pb-Free Packages are Available



ON Semiconductor®

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MARKING DIAGRAMS



QFN-16 MN SUFFIX CASE 485G



Current
Part Marking

16 1 C C ALYW

> Previous Part Marking*

^{*}Previous releases of this device may be marked as shown in this diagram.



TSSOP-16 DT SUFFIX CASE 948F

1

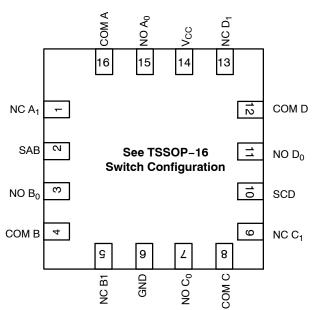
A = Assembly Location

L = Wafer Lot
 Y = Year
 W = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

QFN-16 PACKAGE



FUNCTION TABLE

Select AB or CD	On Channel
L	NC to COM
H	NO to COM

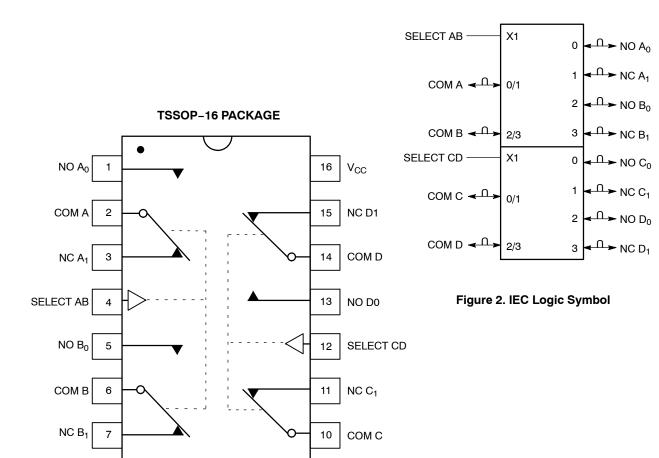


Figure 1. Logic Diagram

GND

NO Co

MAXIMUM RATINGS

Symbol	P	arameter	Value	Unit		
V _{CC}	Positive DC Supply Voltage		-0.5 to +7.0	V		
V _{IS}	Analog Input Voltage (V _{NO} or V _{COM})	Analog Input Voltage (V _{NO} or V _{COM})				
V _{IN}	Digital Select Input Voltage		$-0.5 \le V_{ } \le +7.0$	V		
I _{IK}	DC Current, Into or Out of Any Pin		±50	mA		
P _D	Power Dissipation in Still Air	QFN-16 TSSOP-16	800 450	mW		
T _{STG}	Storage Temperature Range		-65 to +150	°C		
TL	Lead Temperature, 1 mm from Case for	260	°C			
TJ	Junction Temperature Under Bias		+150	°C		
MSL	Moisture Sensitivity		Level 1			
F _R	Flammability Rating	Oxygen Index: 30% - 35%	UL 94-V0 (0.125 in)			
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	2000 200 1000	V		
I _{Latch-Up}	Latch-Up Performance	Above V _{CC} and Below GND at 125°C (Note 4)	±300	mA		
θ_{JA}	Thermal Resistance	QFN-16 TSSOP-16	80 164	°C/W		

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.
- 4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	2.0	5.5	V	
V _{IN}	Digital Select Input Voltage	GND	5.5	V	
V _{IS}	Analog Input Voltage (NC, NO, COM)		GND	V _{CC}	V
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise or Fall Time, SELECT V _{CC} : V _{CC} :	= 3.3 V ± 0.3 V = 5.0 V ± 0.5 V	0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

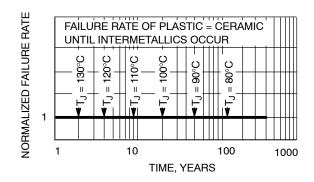


Figure 3. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Condition	V _{CC}	-55°C to 25°C	<85°C	<125°C	Unit
V _{IH}	Minimum High-Level Input		2.0	1.5	1.5	1.5	V
	Voltage, Select Inputs		2.5	1.9	1.9	1.9	
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			5.5	3.85	3.85	3.85	
V _{IL}	Maximum Low-Level Input		2.0	0.5	0.5	0.5	V
	Voltage, Select Inputs		2.5	0.6	0.6	0.6	
			3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			5.5	1.65	1.65	1.65	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	5.5	±0.2	±2.0	±2.0	μΑ
l _{OFF}	Power Off Leakage Current, Select Inputs	V _{IN} = 5.5 V or GND	0	±10	±10	±10	μΑ
Icc	Maximum Quiescent Supply Current	Select and V _{IS} = V _{CC} or GND	5.5	4.0	4.0	8.0	μΑ

DC ELECTRICAL CHARACTERISTICS - Analog Section

				Guaranteed Limit			
Symbol	Parameter	Condition	V _{CC}	-55°C to 25°C	<85°C	<125°C	Unit
R _{ON}	Maximum "ON" Resistance (Figures 17 – 23)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = \text{GND to } V_{CC}$	2.5 3.0	85 45	95 50	105 55	Ω
	,	$I_{\text{IN}}I \leq 10.0 \text{ mA}$	4.5 5.5	30 25	35 30	40 35	
R _{FLAT (ON)}	ON Resistance Flatness (Figures 17 – 23)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{IN}I \le 10.0 \text{ mA}$ $V_{IS} = 1 \text{ V, 2 V, 3.5 V}$	4.5	4	4	5	Ω
I _{NC(OFF)} I _{NO(OFF)}	NO or NC Off Leakage Current (Figure 9)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{NO} \text{ or } V_{NC} = 1.0 \text{ V}_{COM} \text{ 4.5 V}$	5.5	1	10	100	nA
I _{COM(ON)}	COM ON Leakage Current (Figure 9)	$\begin{split} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{NO} \text{ 1.0 V or 4.5 V with } V_{NC} \text{ floating or } \\ &V_{NO} \text{ 1.0 V or 4.5 V with } V_{NO} \text{ floating } \\ &V_{COM} = \text{1.0 V or 4.5 V} \end{split}$	5.5	1	10	100	nA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

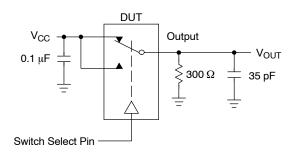
						Guaranteed Maximum Limit						
			v _{cc}	V _{IS}	- 5	5°C to 2	25°C	<85°C		<125°C		
Symbol	Parameter	Test Conditions	(V)	(v)	Min	Тур*	Max	Min	Max	Min	Max	Unit
ton	Turn-On Time	$R_L = 300 \Omega, C_L = 35 pF$	2.5	2.0	5	23	35	5	38	5	41	ns
	(Figures 12 and 13)	(Figures 5 and 6)	3.0	2.0	5	16	24	5	27	5	30	
			4.5	3.0	2	11	16	2	19	2	22	
			5.5	3.0	2	9	14	2	17	2	20	
toff	Turn-Off Time	$R_L = 300 \Omega, C_L = 35 pF$	2.5	2.0	1	7	12	1	15	1	18	ns
	(Figures 12 and 13)	(Figures 5 and 6)	3.0	2.0	1	5	10	1	13	1	16	
			4.5	3.0	1	4	6	1	9	1	12	
			5.5	3.0	1	3	5	1	8	1	11	
t _{BBM}	Minimum Break-Before-Make	V _{IS} = 3.0 V (Figure 4)	2.5	2.0	1	12		1		1		ns
	Time	$R_L = 300 \Omega$, $C_L = 35 pF$	3.0	2.0	1	11		1		1		
			4.5	3.0	1	6		1		1		
			5.5	3.0	1	5		1		1		

		Typical @ 25, V _{CC} = 5.0 V	~F
C _{IN}	Maximum Input Capacitance, Select Input	8	pF
C _{NO} or C _{NC}	Analog I/O (switch off)	10	
C _{COM}	Common I/O (switch off)	10	
C _(ON)	Feedthrough (switch on)	20	

^{*}Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

			V _{CC}	Typical	
Symbol	Parameter	Condition	v	25°C	Unit
BW	Maximum On-Channel -3dB	V _{IN} = 0 dBm	3.0	145	MHz
	Bandwidth or Minimum Frequency Response (Figure 11)	V _{IN} centered between V _{CC} and GND	4.5	170	
	Tresponse (Figure 11)	(Figure 7)	5.5	175	1
V _{ONL}	Maximum Feedthrough On Loss	V _{IN} = 0 dBm @ 100 kHz to 50 MHz	3.0	-3	dB
		V _{IN} centered between V _{CC} and GND	4.5	-3	1
		(Figure 7)	5.5	-3	1
V _{ISO}	Off-Channel Isolation (Figure 10)	f = 100 kHz; V _{IS} = 1 V RMS	3.0	-93	dB
		V _{IN} centered between V _{CC} and GND	4.5	-93	1
		(Figure 7)	5.5	-93	1
Q	Charge Injection Select Input to	V _{IN =} V _{CC to} GND, F _{IS} = 20 kHz			рC
	Common I/O (Figure 15)	$t_r = t_f = 3 \text{ ns}$	3.0	1.5	1
		$R_{IS} = 0 \Omega$, $C_L = 1000 pF$	5.5	3.0	1
		$Q = C_L * \Delta V_{OUT}$			
		(Figure 8)			
THD	Total Harmonic Distortion THD +	F_{IS} = 20 Hz to 100 kHz, R_L = Rgen = 600 Ω , C_L = 50 pF			%
	Noise (Figure 14)	$V_{IS} = 5.0 V_{PP}$ sine wave	5.5	0.1	1
VCT	Channel-to-Channel Crosstalk	f = 100 kHz; V _{IS} = 1 V RMS			dB
		V _{IN} centered between V _{CC} and GND	5.5	-90	
		(Figure 7)	3.0	-90	1



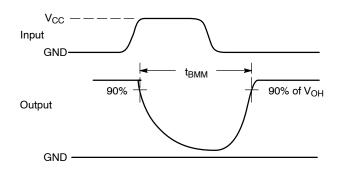
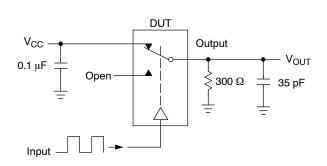


Figure 4. t_{BBM} (Time Break–Before–Make)



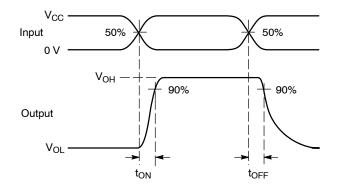
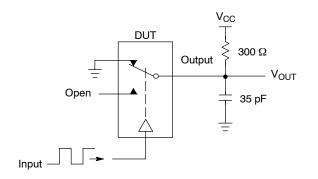


Figure 5. t_{ON}/t_{OFF}



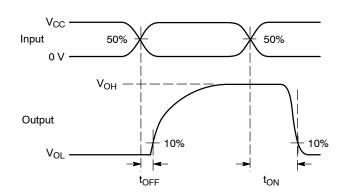
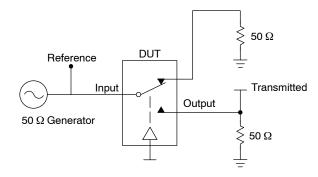


Figure 6. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$V_{ISO} = Off Channel Isolation = 20 Log \left(\frac{V_{OUT}}{V_{IN}}\right)$$
 for V_{IN} at 100 kHz

 $V_{ONL} = On \ Channel \ Loss = 20 \ Log \ \left(\frac{V_{OUT}}{V_{IN}}\right) for \ V_{IN} \ at \ 100 \ kHz \ to \ 50 \ MHz$

Bandwidth (BW) = the frequency 3 dB below V_{ONL} V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

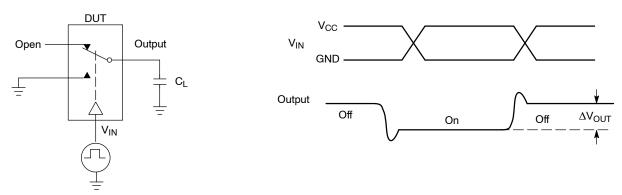


Figure 8. Charge Injection: (Q)

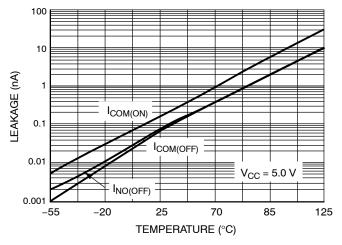
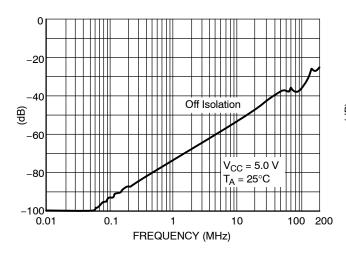


Figure 9. Switch Leakage vs. Temperature



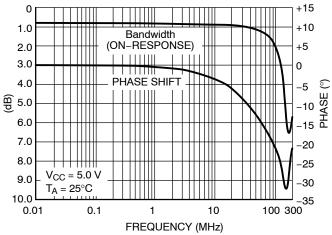
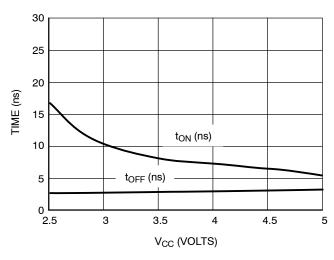
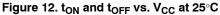


Figure 10. Off-Channel Isolation

Figure 11. Typical Bandwidth and Phase Shift





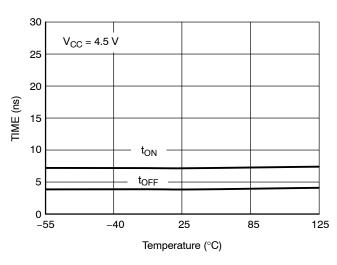


Figure 13. t_{ON} and t_{OFF} vs. Temp

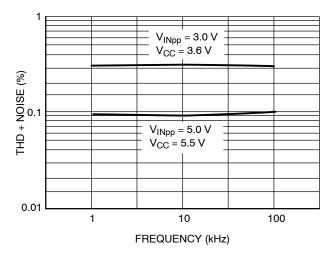


Figure 14. Total Harmonic Distortion Plus Noise vs. Frequency

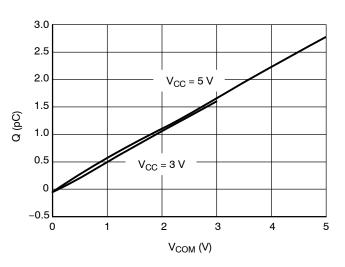
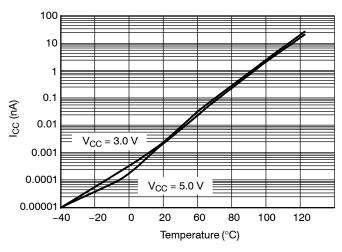


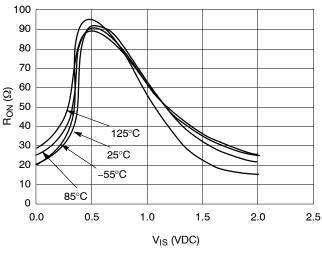
Figure 15. Charge Injection vs. COM Voltage



100 $V_{CC} = 2.0 \text{ V}$ 80 60 Ron (Q) V_{CC} = 2.5 V 40 $V_{CC} = 3.0 \text{ V}$ V_{CC} = 4.0 V 20 V_{CC} = 5.5 V 0.0 1.0 2.0 3.0 4.0 5.0 6.0 V_{IS} (VDC)

Figure 16. I_{CC} vs. Temp, V_{CC} = 3 V & 5 V

Figure 17. R_{ON} vs. V_{CC} , Temp = 25°C



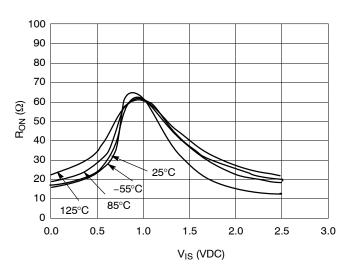
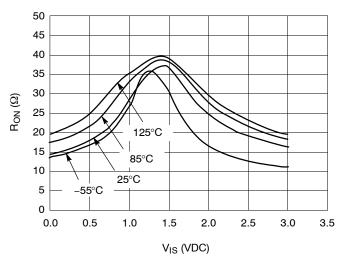


Figure 18. R_{ON} vs Temp, V_{CC} = 2.0 V

Figure 19. R_{ON} vs. Temp, V_{CC} = 2.5 V



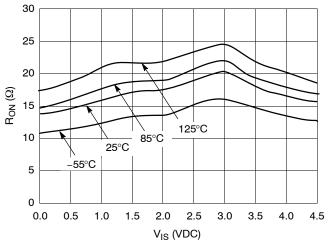
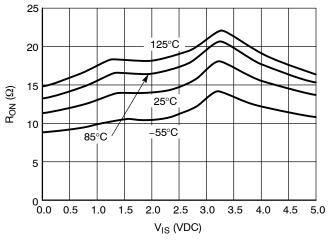
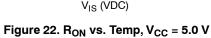


Figure 20. R_{ON} vs. Temp, V_{CC} = 3.0 V

Figure 21. R_{ON} vs. Temp, V_{CC} = 4.5 V





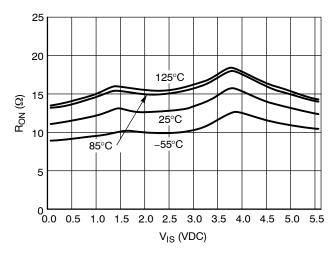


Figure 23. R_{ON} vs. Temp, V_{CC} = 5.5 V

DEVICE ORDERING INFORMATION

		Devi	ce Nomenc	e Nomenclature			
Device	Circuit Indicator	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Shipping [†]
NLAS44599DT	NL	AS	44599	DT		TSSOP-16*	96 / Unit Rail
NLAS44599DTR2	NL	AS	44599	DT	R2	TSSOP-16*	2500 / Tape & Reel
NLAS44599MN	NL	AS	44599	MN		QFN-16	124 Unit / Rail
NLAS44599MNG	NL	AS	44599	MN		QFN-16 (Pb-Free)	124 Unit / Rail
NLAS44599MNR2	NL	AS	44599	MN	R2	QFN-16	2500 / Tape & Reel
NLAS44599MNR2G	NL	AS	44599	MN	R2	QFN-16 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

回

TOP VIEW

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SIDE VIEW

DETAIL B

LEA

A1

PIN ONE

LOCATION

2X 0.10 C

2X 0.10 C

// 0.05 C

□ 0.05 C

NOTE 4





Α

В

SEATING PLANE

C

Ē

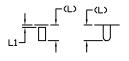
DATE 08 OCT 2021

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS.
 THE TERMINALS.



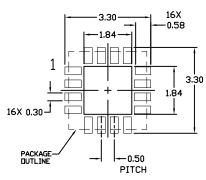
DETAIL B
ALTERNATE
CONSTRUCTIONS

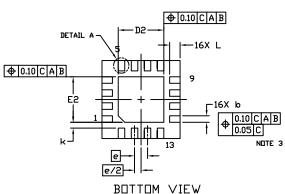


DETAIL A
ALTERNATE TERMINAL
CONSTRUCTIONS

	MILLIME	TERS				
DIM	MIN.	N□M.	MAX.			
Α	0.80	0.90	1.00			
A1	0.00	0.03	0.05			
A3		0.20 REF				
b	0.18	0.24	0.30			
D		3.00 BSC	;			
DS	1.65	1.75	1.85			
Ε		3.00 BSC	;			
E2	1.65	1.75	1.85			
e	0.50 BSC					
k	0.18 TYP					
L	0.30	0.40	0.50			
L1	0.00	0.08	0.15			

MOUNTING FOOTPRINT





GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code A = Assembly Location

L = Wafer Lot
Y = Year
W = Work Week
■ Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON04795D	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	QFN16 3X3, 0.5P		PAGE 1 OF 1			

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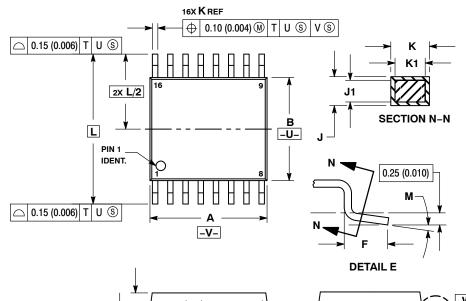
-T- SEATING PLANE





TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ы	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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